

Silicon PNP Power Transistors

MJ15002

DESCRIPTION

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- With TO-3 package
- Complement to type MJ15001
- Excellent safe operating area

APPLICATIONS

- For high power audio,disk head positioners and other linear applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

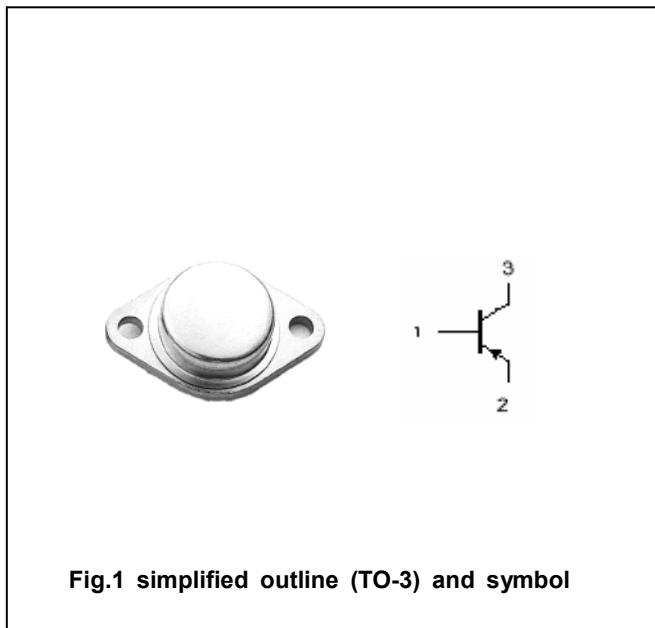


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T<sub>C</sub>=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-140	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-140	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-15	A
I <sub>B</sub>	Base current		-5	A
I <sub>E</sub>	Emitter current		20	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25°C	250	W
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance junction to case	0.875	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =-0.2A ; I <sub>B</sub> =0	-140			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-4A ; I <sub>B</sub> =-0.4A			-1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-2V			-2.0	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-140V ; I <sub>B</sub> =0			-0.25	mA
I <sub>CEX</sub>	Collector cut-off current	V <sub>CE</sub> =-140V ; V <sub>BE(off)</sub> =-1.5V T <sub>C</sub> =150°C			-0.1 -2.0	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-4A ; V <sub>CE</sub> =-2V	25		150	
I <sub>S/b</sub>	Second breakdown collector current With base forward biased	V <sub>CE</sub> =-40Vdc, t=1 s, Nonrepetitive	-5			A
		V <sub>CE</sub> =-100Vdc, t=1 s, Nonrepetitive	-0.5			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1.0MHz			1000	pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-10V ; f=0.5MHz	2			MHz

